

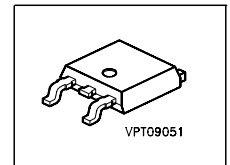
### Cool MOS™ Power Transistor

#### Feature

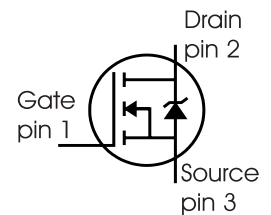
- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance

$V_{DS}$	800	V
$R_{DS(on)}$	1.3	$\Omega$
$I_D$	4	A

P-TO252-3-1



Type	Package	Ordering Code	Marking
SPD04N80C3	P-TO252-3-1	Q47040-S4563	04N80C3



#### Maximum Ratings, at $T_C = 25^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25^\circ\text{C}$ $T_C = 100^\circ\text{C}$	$I_D$	4 2.5	A
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_{D\ puls}$	12	
Avalanche energy, single pulse $I_D=0.8\text{A}$ , $V_{DD}=50\text{V}$	$E_{AS}$	170	mJ
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>1)</sup> $I_D=4\text{A}$ , $V_{DD}=50\text{V}$	$E_{AR}$	0.1	
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	4	A
Gate source voltage	$V_{GS}$	$\pm 20$	V
Power dissipation, $T_C = 25^\circ\text{C}$	$P_{tot}$	63	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$^\circ\text{C}$

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 640\text{ V}, I_D = 4\text{ A}, T_j = 125\text{ °C}$	$dv/dt$	50	V/ns

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	2	K/W
SMD version, device on PCB: @ min. footprint	$R_{thJA}$	-	-	75	
@ 6 cm <sup>2</sup> cooling area <sup>2)</sup>		-	-	50	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s <sup>3)</sup>	$T_{sold}$	-	-	260	°C

**Electrical Characteristics**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=0.25mA$	800	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0V, I_D=4A$	-	870	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=240\mu A, V_{GS}=V_{DS}$	2.1	3	3.9	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=800V, V_{GS}=0V,$ $T_j=25\text{ °C},$ $T_j=150\text{ °C}$	-	0.5	10	$\mu A$
			-	-	100	
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20V, V_{DS}=0V$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=2.5A,$ $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	-	1.1	1.3	$\Omega$
			-	3	-	
Gate input resistance	$R_G$	$f=1MHz, \text{open Drain}$	-	0.7	-	

**Electrical Characteristics** , at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 2.5\text{A}$	-	3	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$	-	570	-	pF
Output capacitance	$C_{oss}$		-	240	-	
Reverse transfer capacitance	$C_{rss}$		-	12	-	
Effective output capacitance, <sup>4)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 0\text{V to } 480\text{V}$	-	15.6	-	pF
Effective output capacitance, <sup>5)</sup> time related	$C_{o(tr)}$		-	33.7	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 400\text{V}$ , $V_{GS} = 0/10\text{V}$ , $I_D = 4\text{A}$ , $R_G = 22\Omega$	-	25	-	ns
Rise time	$t_r$		-	15	-	
Turn-off delay time	$t_{d(off)}$		-	65	75	
Fall time	$t_f$		-	12	16	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 640\text{V}$ , $I_D = 4\text{A}$	-	2.4	-	nC
Gate to drain charge	$Q_{gd}$		-	11	-	
Gate charge total	$Q_g$	$V_{DD} = 640\text{V}$ , $I_D = 4\text{A}$ , $V_{GS} = 0\text{ to } 10\text{V}$	-	20	26	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 640\text{V}$ , $I_D = 4\text{A}$	-	6	-	V

<sup>1</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>2</sup> Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

<sup>3</sup> Soldering temperature for TO-263: 220°C, reflow

<sup>4</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

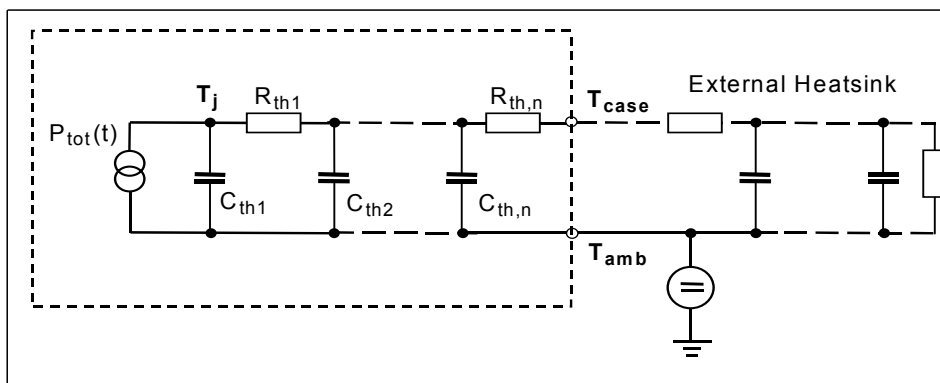
<sup>5</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	$I_S$	$T_C=25^\circ\text{C}$	-	-	4	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	12	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=640\text{V}, I_F=I_S,$	-	520	-	ns
Reverse recovery charge	$Q_{rr}$	$di_F/dt=100\text{A}/\mu\text{s}$	-	4	-	$\mu\text{C}$
Peak reverse recovery current	$I_{rrm}$		-	12	-	A
Peak rate of fall of reverse recovery current	$di_{rr}/dt$		-	300	-	$\text{A}/\mu\text{s}$

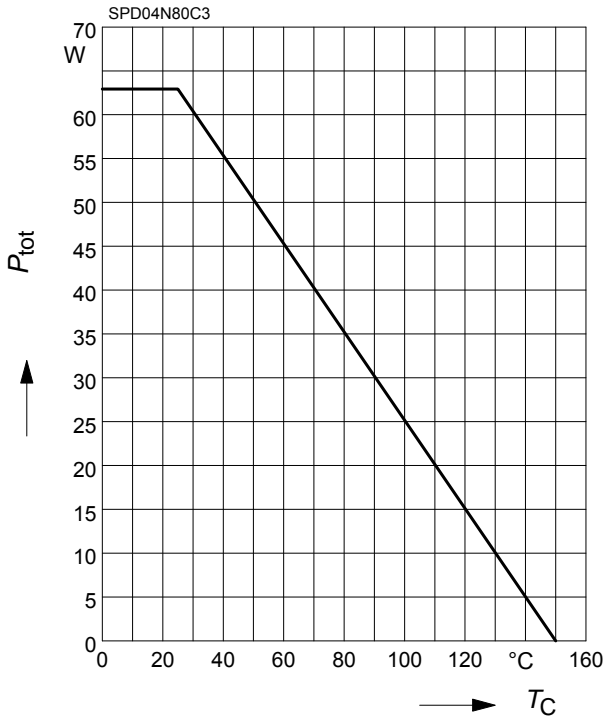
**Typical Transient Thermal Characteristics**

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
$R_{th1}$	0.033	K/W	$C_{th1}$	0.00008691	Ws/K
$R_{th2}$	0.063		$C_{th2}$	0.0003336	
$R_{th3}$	0.113		$C_{th3}$	0.0004755	
$R_{th4}$	0.432		$C_{th4}$	0.001405	
$R_{th5}$	0.423		$C_{th5}$	0.003503	
$R_{th6}$	0.14		$C_{th6}$	0.036	



**1 Power dissipation**

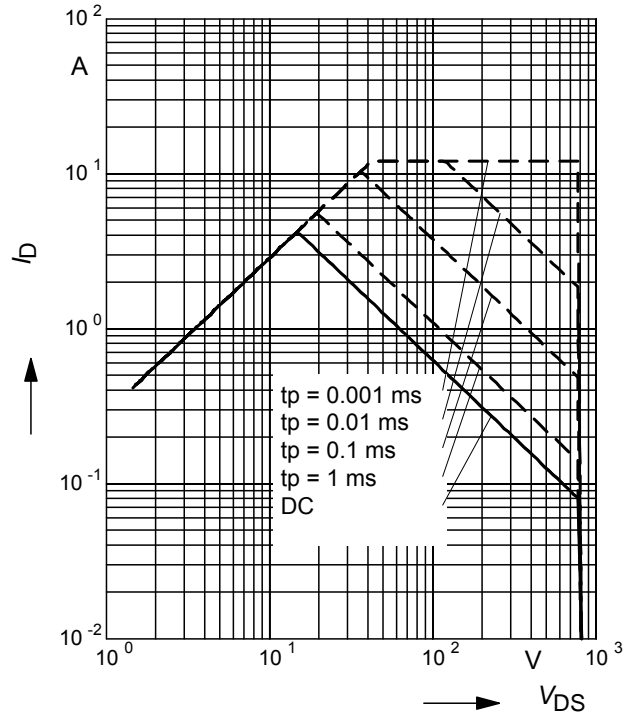
$$P_{tot} = f(T_C)$$



**2 Safe operating area**

$$I_D = f(V_{DS})$$

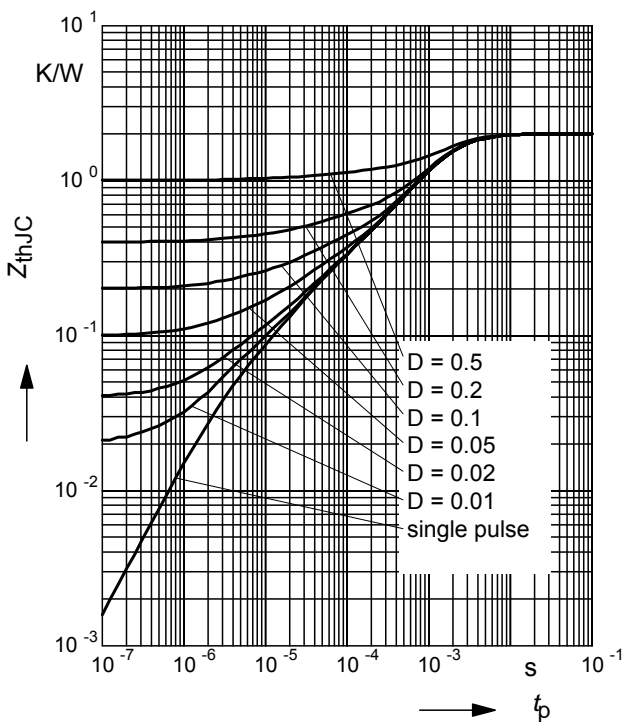
parameter :  $D = 0$  ,  $T_C = 25^\circ\text{C}$



**3 Transient thermal impedance**

$$Z_{thJC} = f(t_p)$$

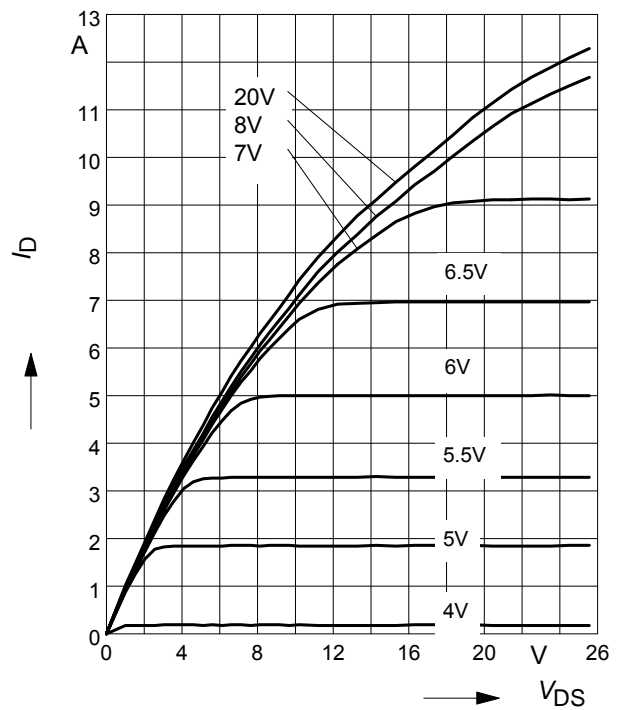
parameter:  $D = t_p/T$



**4 Typ. output characteristic**

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

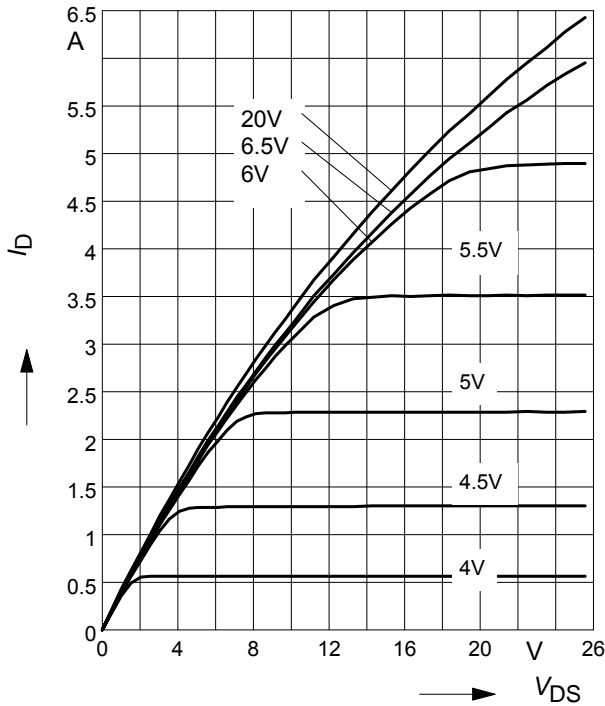
parameter:  $t_p = 10 \mu\text{s}$  ,  $V_{GS}$



**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$

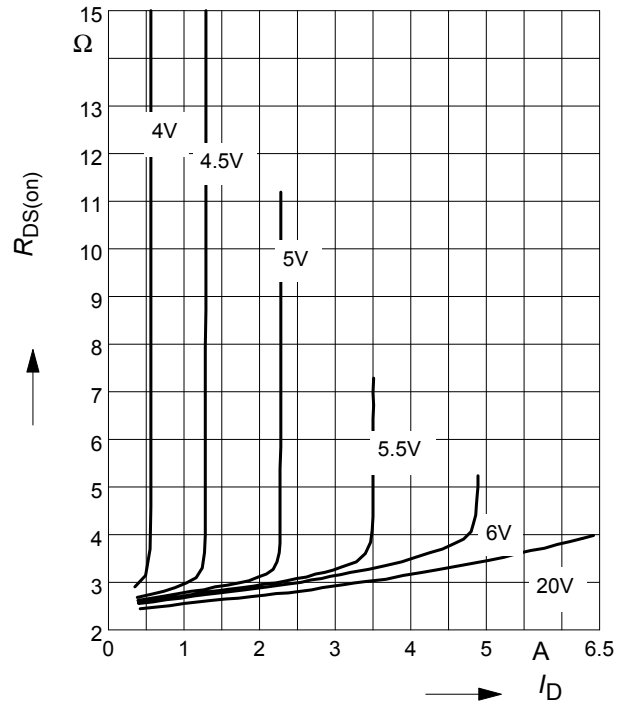
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$

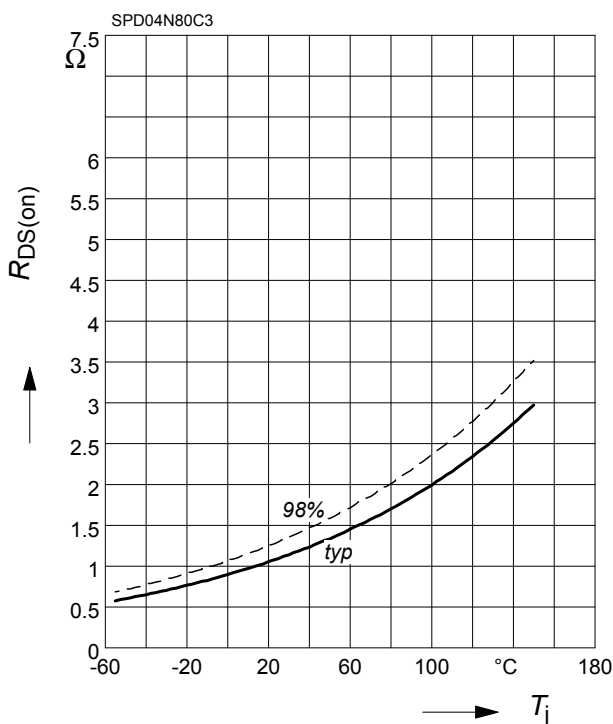
parameter:  $T_j = 150^\circ\text{C}, V_{GS}$



**7 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j)$

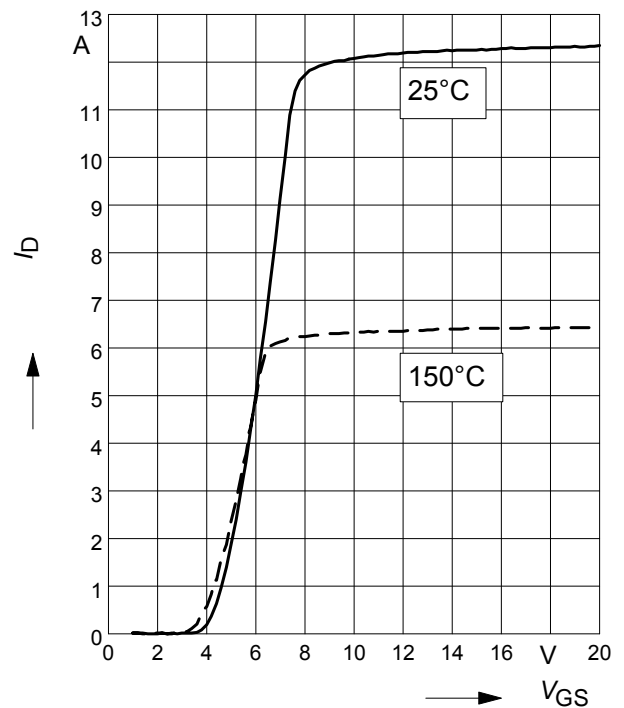
parameter:  $I_D = 2.5 \text{ A}, V_{GS} = 10 \text{ V}$



**8 Typ. transfer characteristics**

$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$

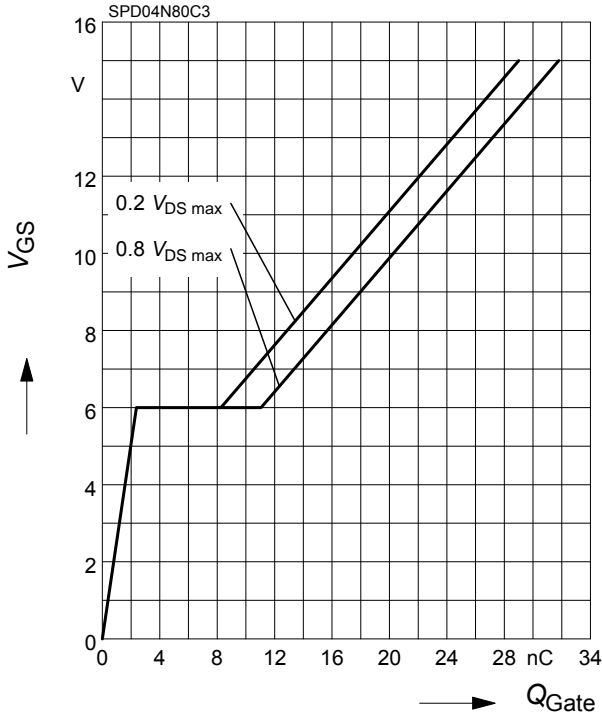
parameter:  $t_p = 10 \mu\text{s}$



**9 Typ. gate charge**

$$V_{GS} = f(Q_{Gate})$$

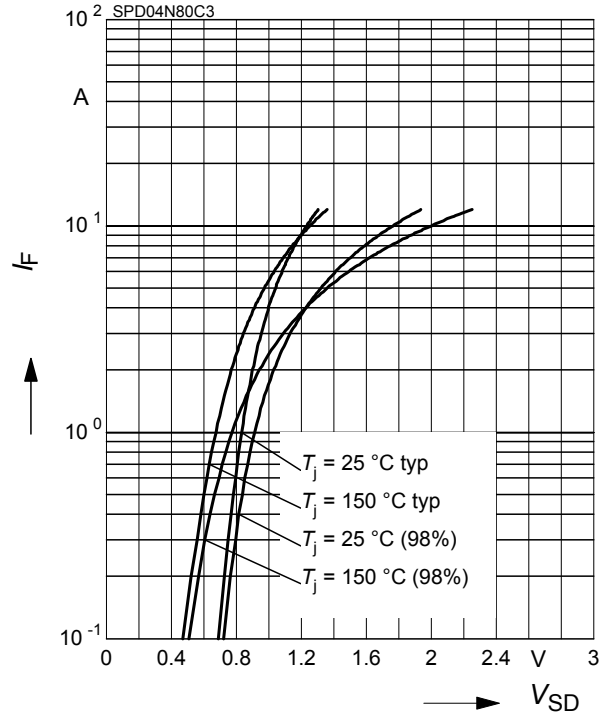
parameter:  $I_D = 4\text{ A}$  pulsed



**10 Forward characteristics of body diode**

$$I_F = f(V_{SD})$$

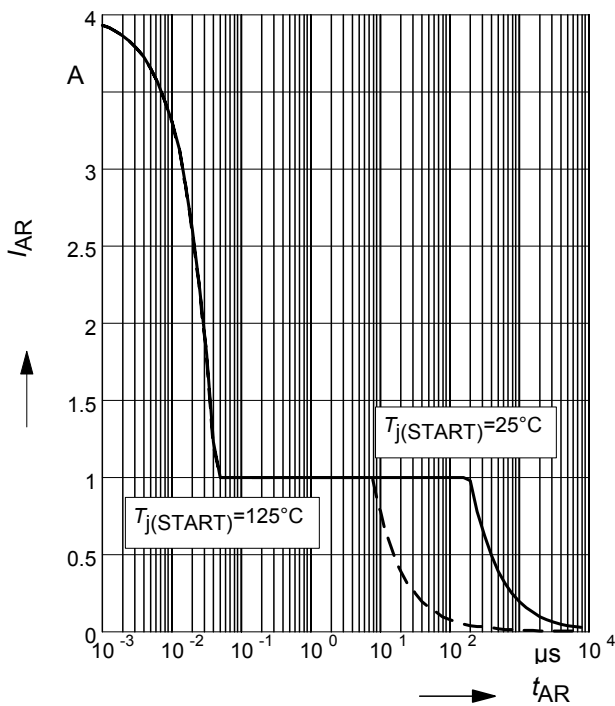
parameter:  $T_j, t_p = 10\ \mu\text{s}$



**11 Avalanche SOA**

$$I_{AR} = f(t_{AR})$$

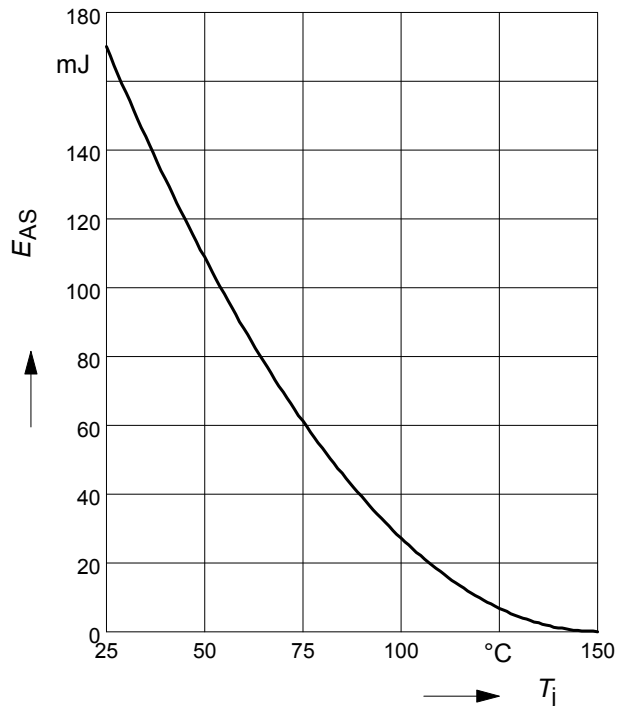
par.:  $T_j \leq 150\text{ °C}$



**12 Avalanche energy**

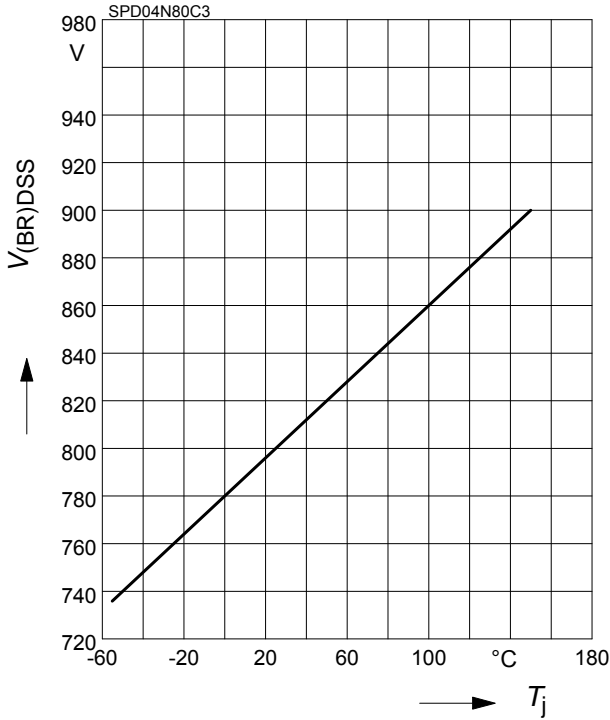
$$E_{AS} = f(T_j)$$

par.:  $I_D = 0.8\text{ A}, V_{DD} = 50\text{ V}$



**13 Drain-source breakdown voltage**

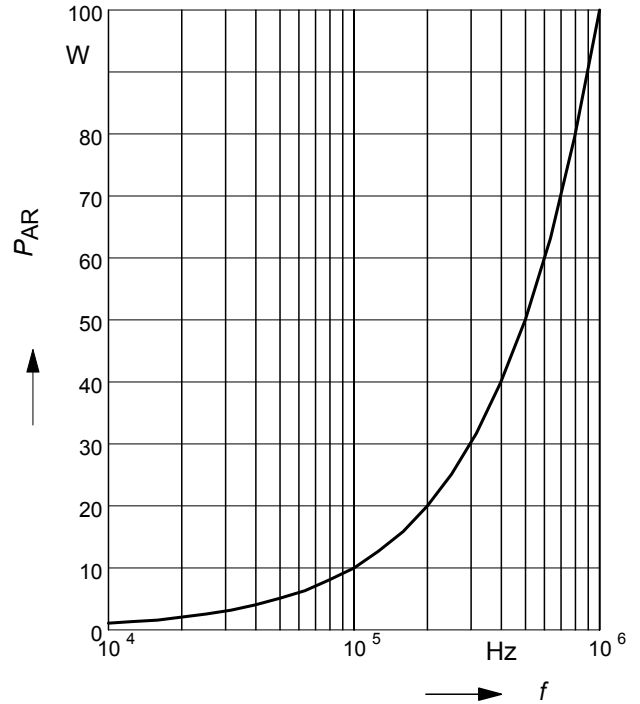
$$V_{(BR)DSS} = f(T_j)$$



**14 Avalanche power losses**

$$P_{AR} = f(f)$$

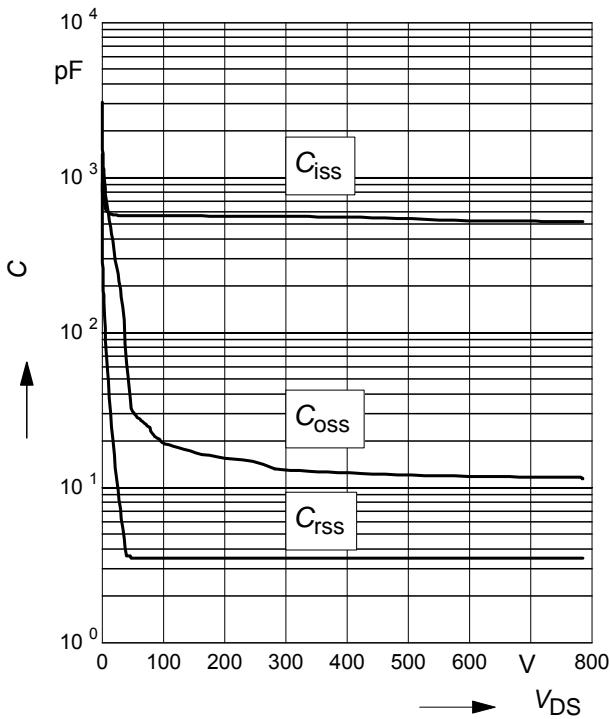
parameter:  $E_{AR}=0.1\text{mJ}$



**15 Typ. capacitances**

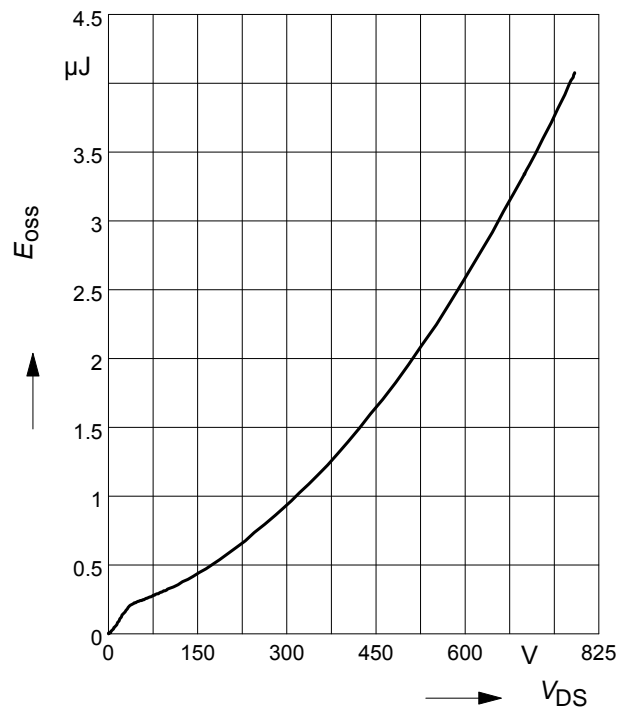
$$C = f(V_{DS})$$

parameter:  $V_{GS}=0\text{V}$ ,  $f=1\text{ MHz}$



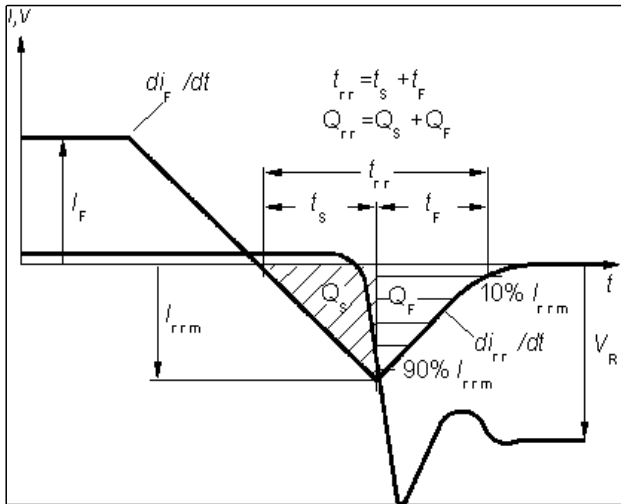
**16 Typ.  $C_{OSS}$  stored energy**

$$E_{OSS} = f(V_{DS})$$

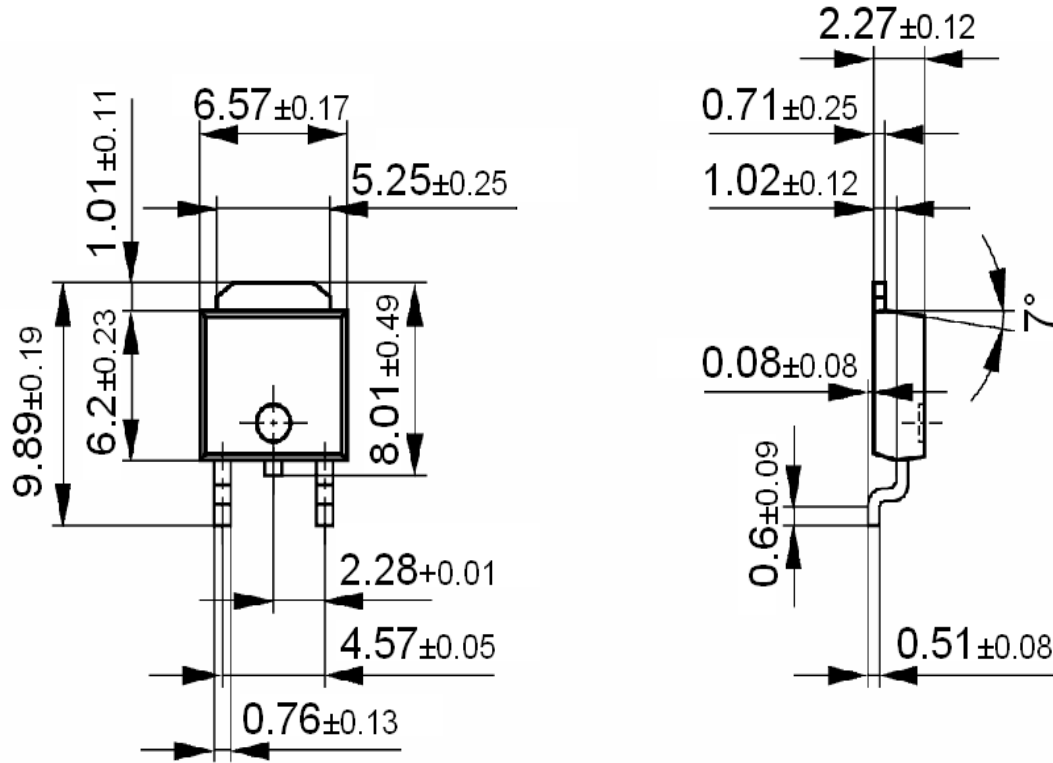




Definition of diodes switching characteristics



P-TO-252-3-1 (D-PAK)



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